

Nanostructured thin films for Meissner-Effect Transition-Edge-Sensor Devices

Presented by

Patrick Finnegan

Christian L. Arrington, Chris St John, and Steve M. Carr

Sandia National Laboratories, Albuquerque, New Mexico



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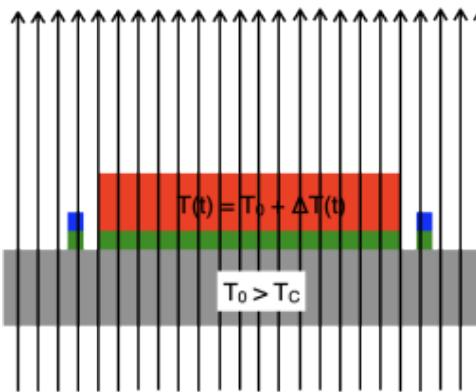
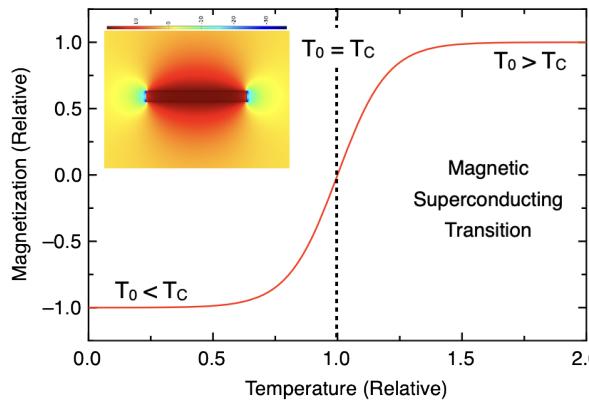
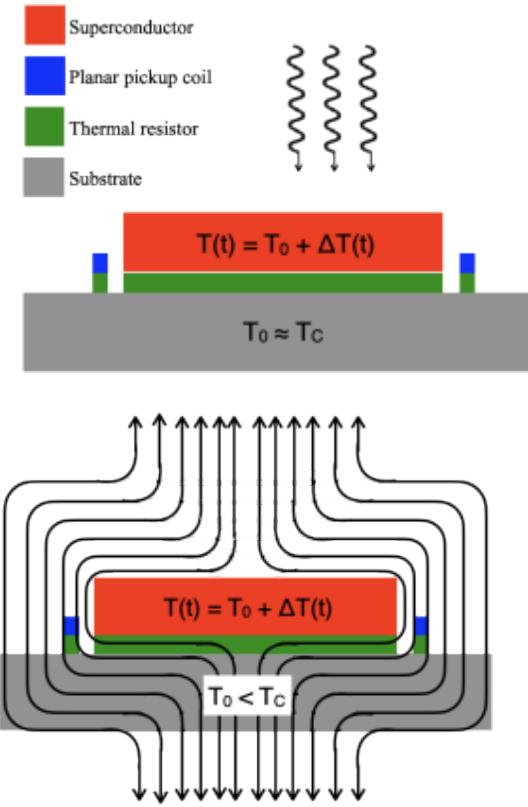
Superconductor
Planar pickup coil
Thermal resistor
Substrate

$T(t) = T_0 + \Delta T(t)$

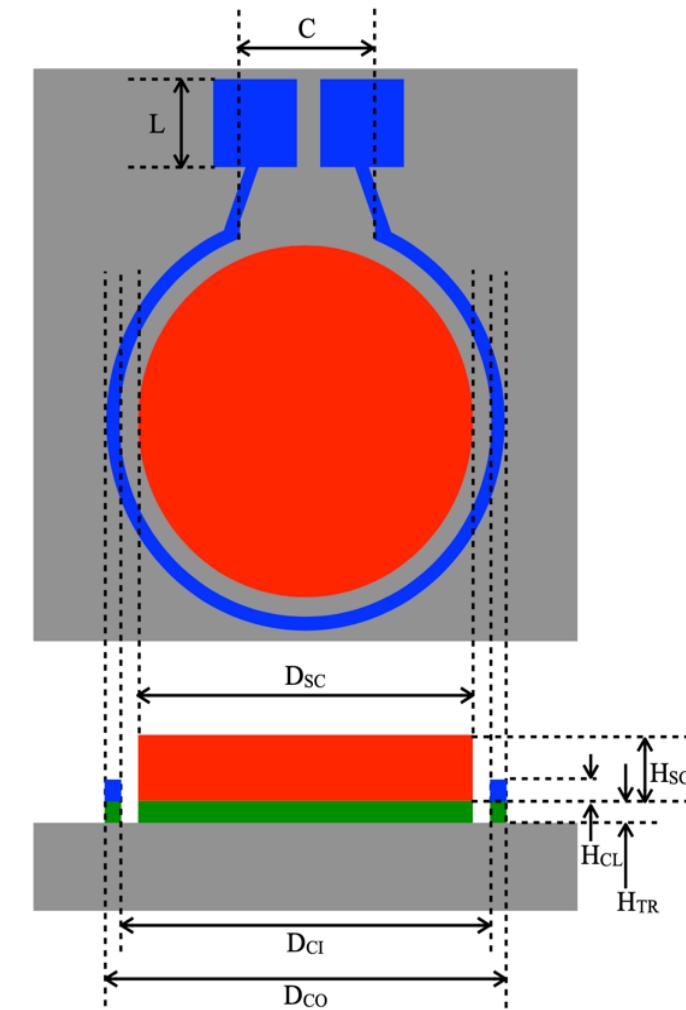
$T_0 \approx T_c$



Meissner-Effect Transition-Edge-Sensor (ME-TES): Introduction



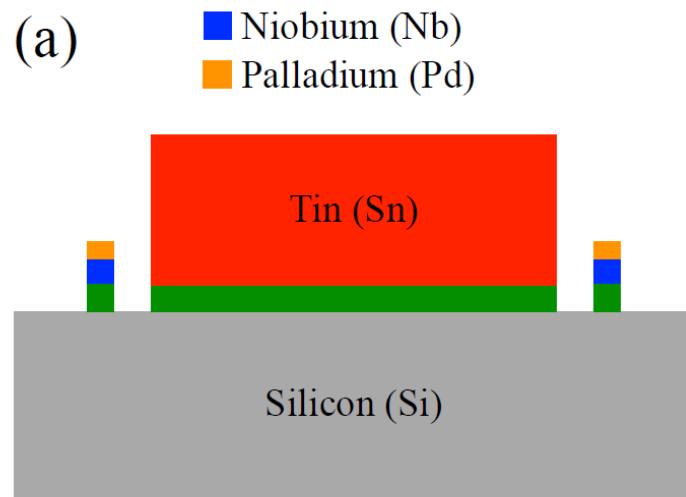
- An ME-TES microcalorimeter employs thermal detection of radiation, as shown schematically above with incident radiation as wavy lines, in particular gamma-ray radiation.



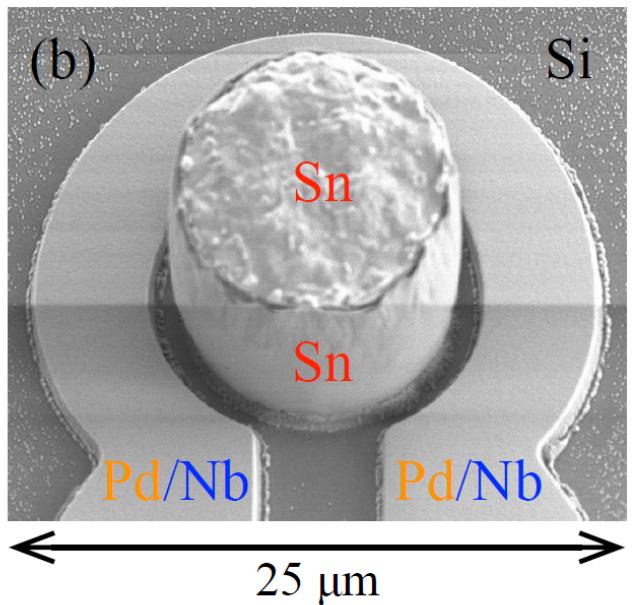
$$S = (D_{CI} - D_{SC}) / 2 = \text{Separation or gap between outer diameter of tin and inner diameter of niobium coil.}$$

$$W = (D_{CO} - D_{CI}) / 2 = \text{Width of niobium coil.}$$

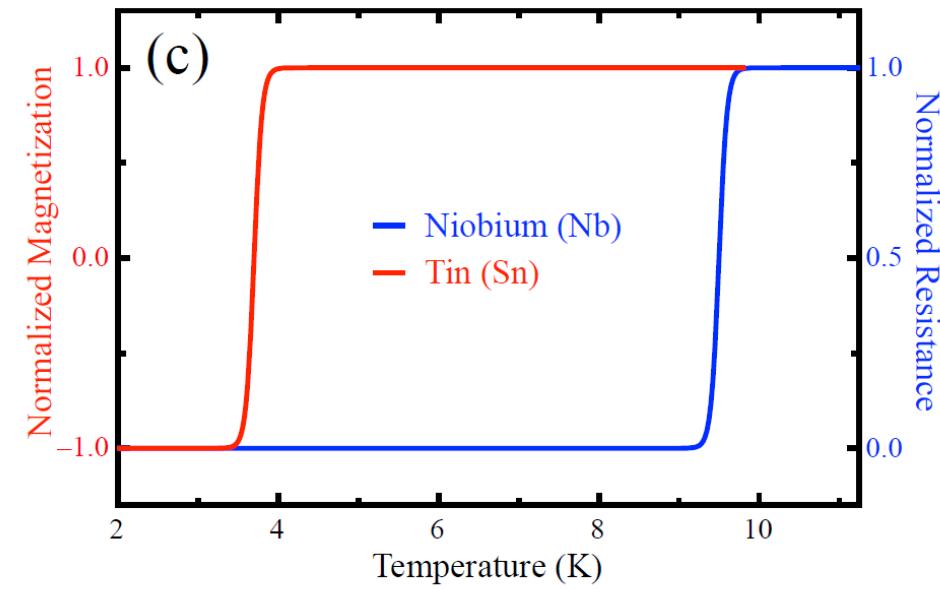
Meissner-effect transition edge sensor (ME-TES)



ME-TES device
schematic cross-
sectional image.

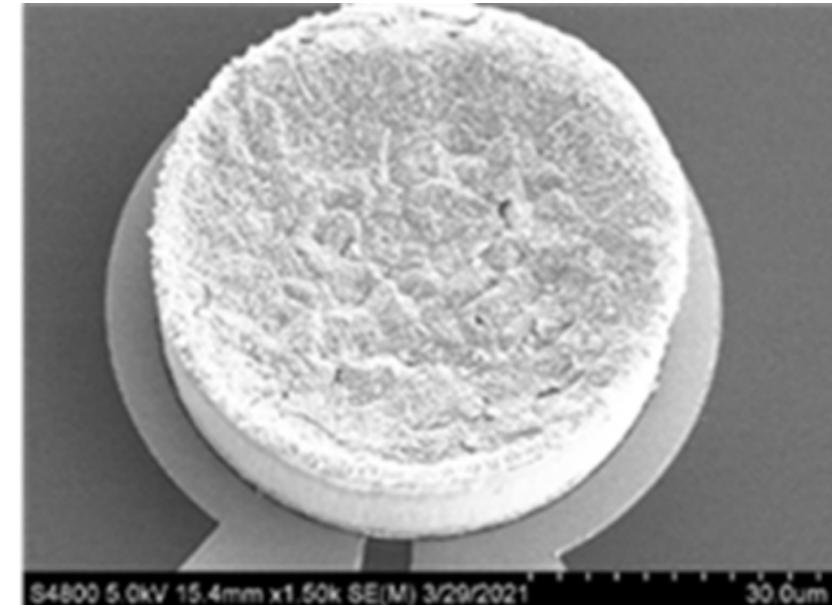
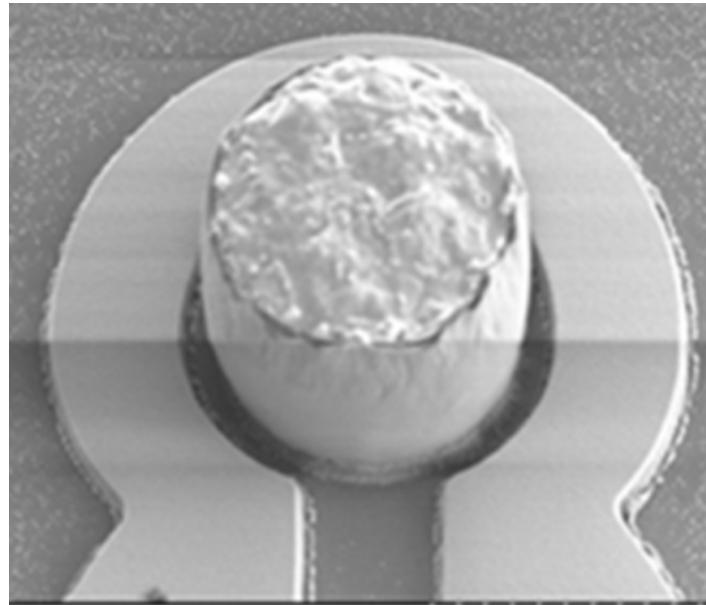
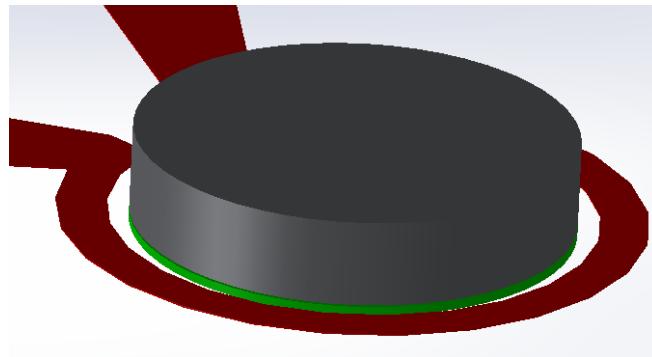


Scanning Electron
Microscope (SEM)
micrograph of a completed
ME-TES device



Operation intended to be at the
Sn magnetic superconducting
range while the Nb is fully
superconducting

Device size and geometries



Scanning Electron Micrograph (SEM) images of completed devices (a)
 $D_{sc} = 10 \mu\text{m}$ and $H_{sc} = 10 \mu\text{m}$ and (b) $D_{sc} = 50 \mu\text{m}$ and $H_{sc} = 10 \mu\text{m}$.

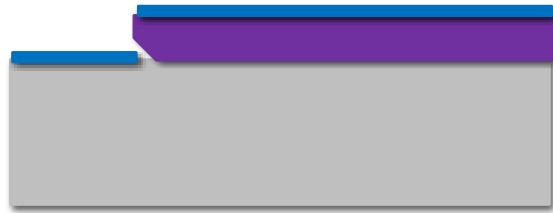
Pick up coils: “Lift off” and “etch” microfabrication



**Niobium metal
deposition to pattern
coils**

**Photoresist with re-entrant
profile**

silicon substrate

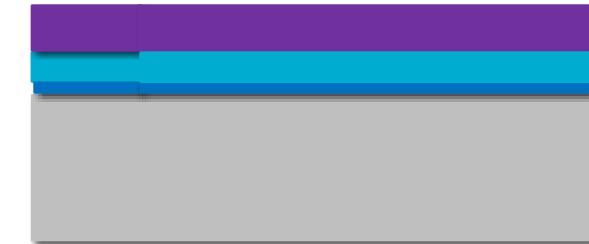


Photoresist

Silicon oxide

**Niobium metal
deposition**

silicon substrate

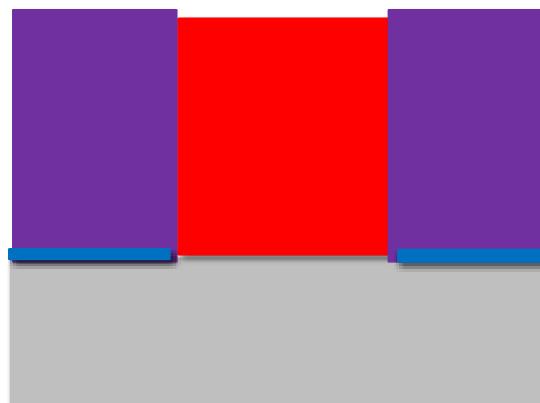


Tin metal deposition

**Photoresist with straight
sidewall**

Niobium metal

Silicon substrate

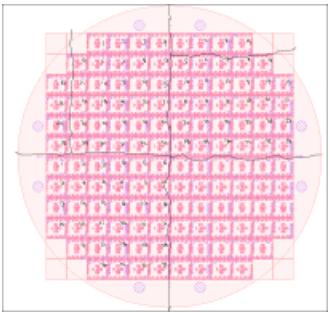


ME-TES Fabrication layout

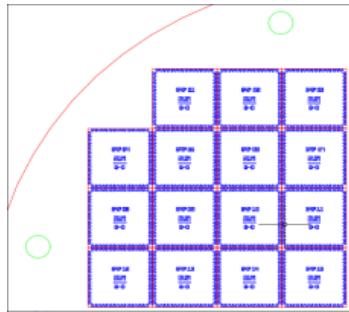


- 150 mm silicon nitride wafers
- Layer 1 defines Al/Nb/Pd superconductor
- Layer 2 defines electroplated tin disc
- Electroplating tin one quarter wafer at a time after
- Microscopy, SEM, XRF, and EDS for analysis

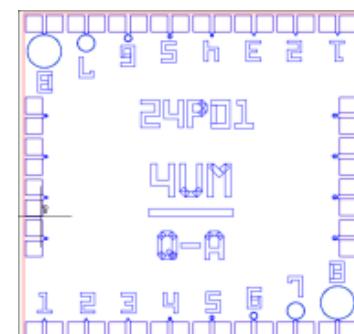
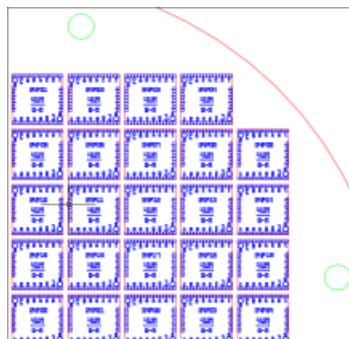
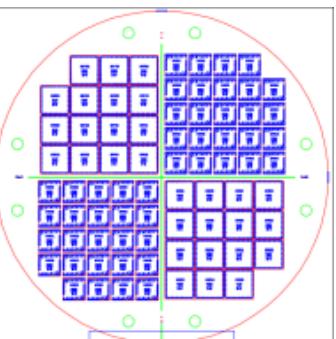
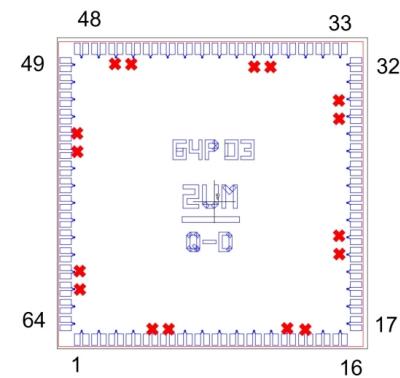
Wafer



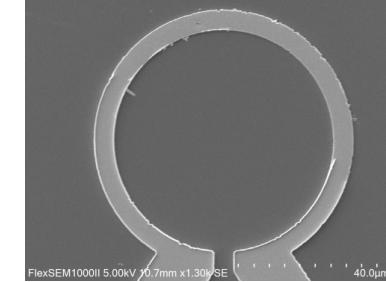
1/4 wafer



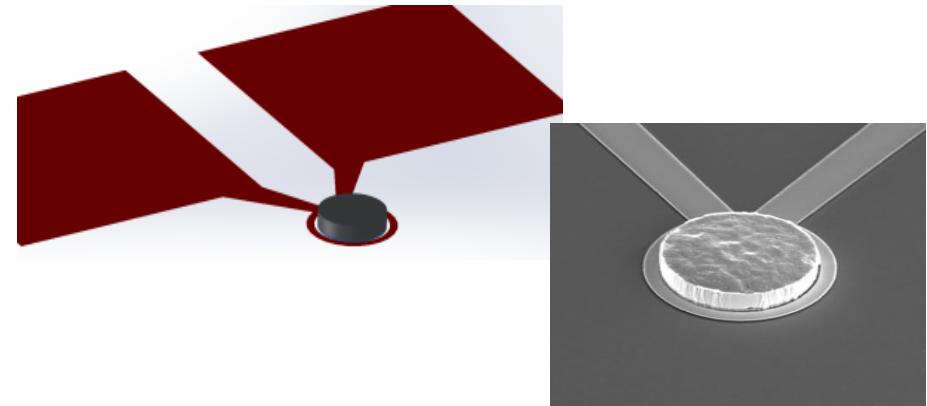
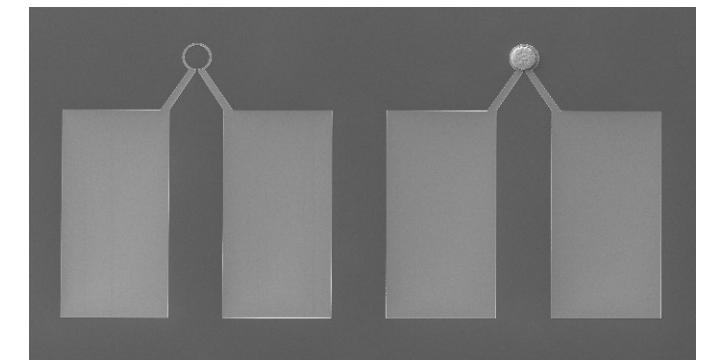
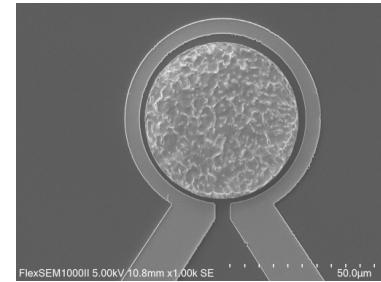
Die



Device without tin (pickup coil)

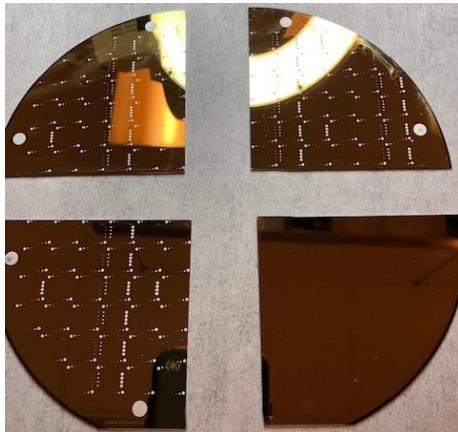
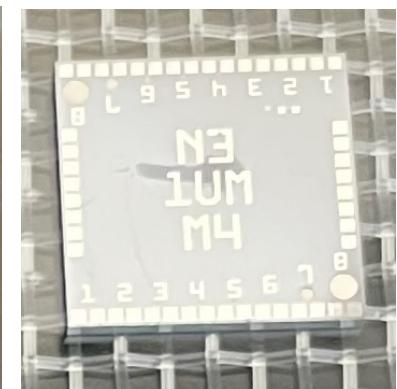
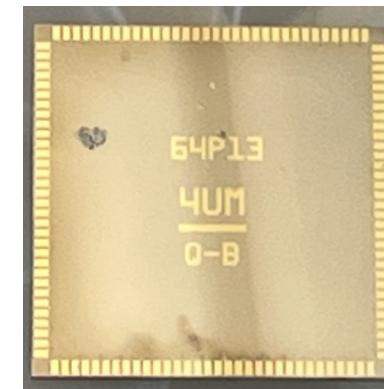
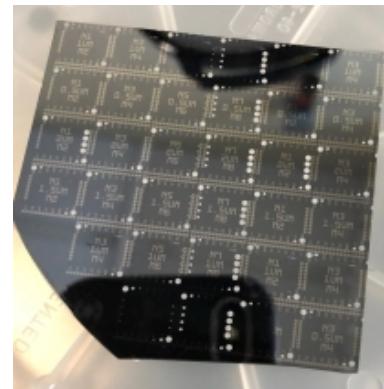
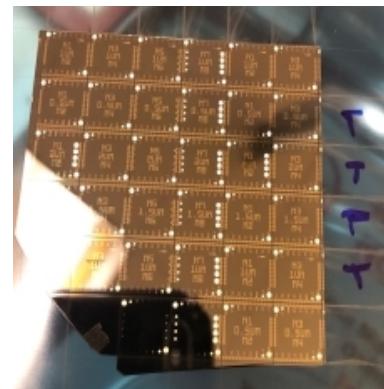
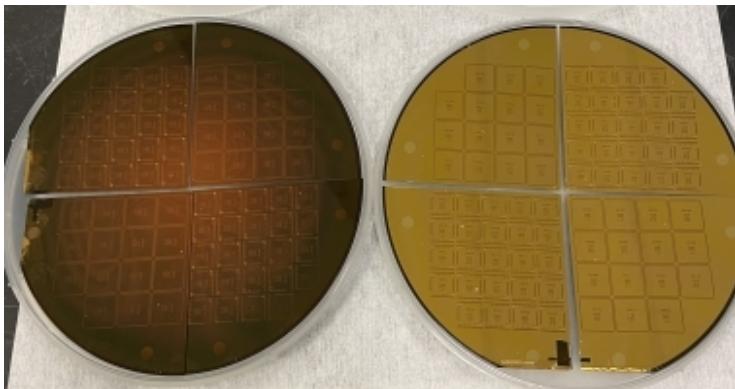


Device with tin

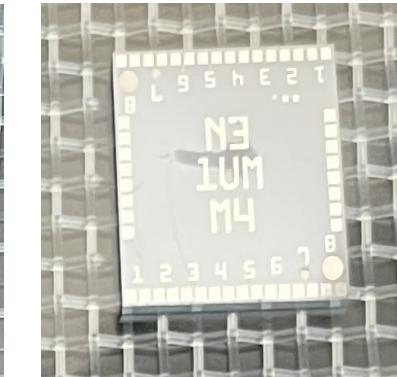
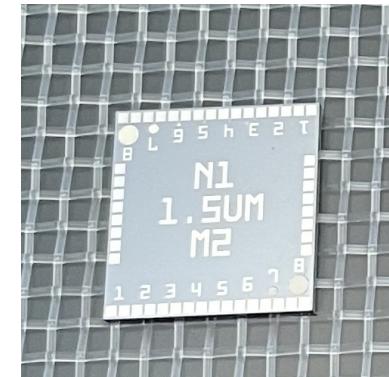


Wafer

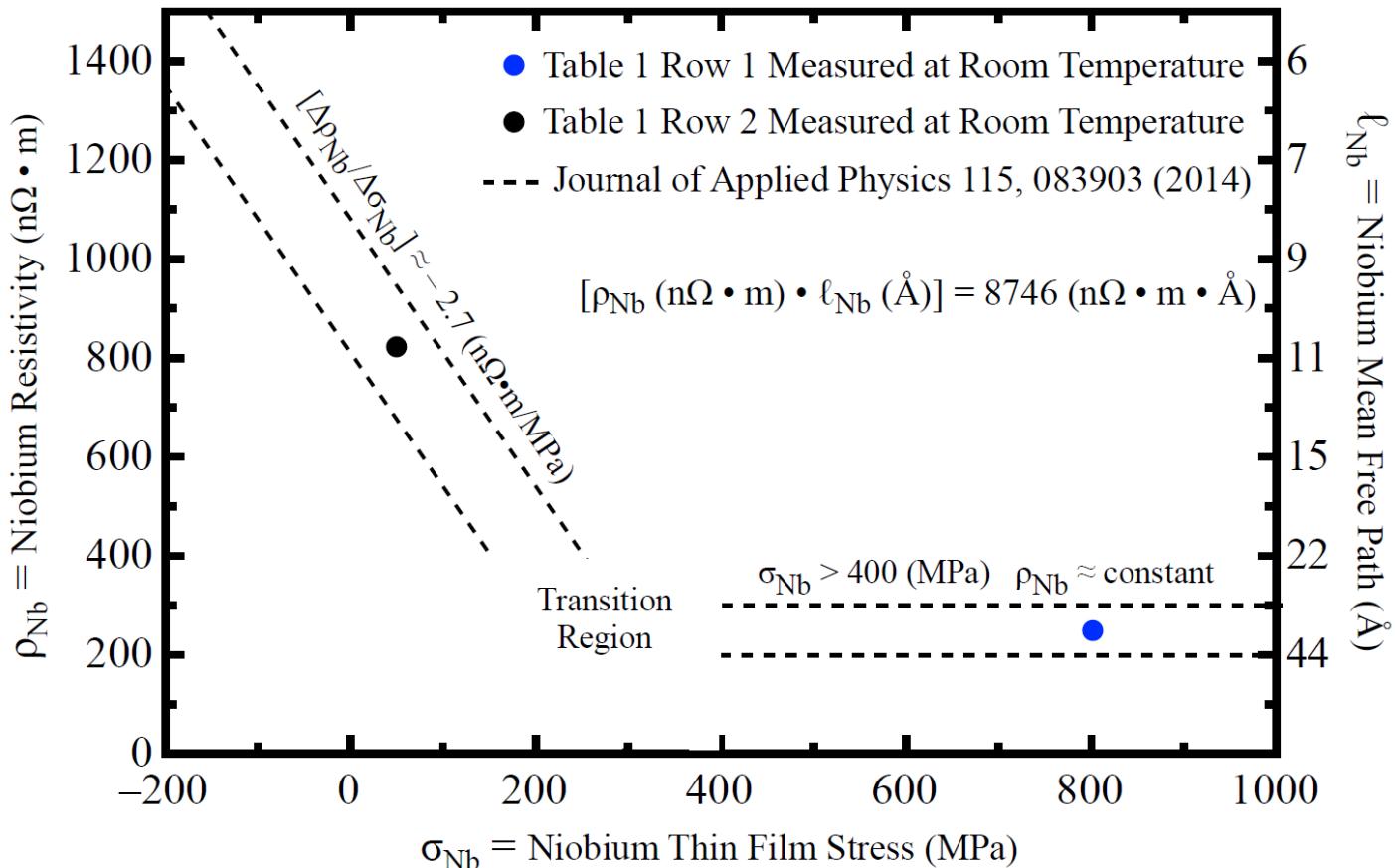
Quarter wafer

Die/device level

Diced quarter wafer



Nb Film stress vs. resistivity at room temperature



Henry et al, Stress dependent oxidation of sputtered niobium and effects on superconductivity JAP 115,083903 (2014)

Deposition parameters and resulting film resistivity

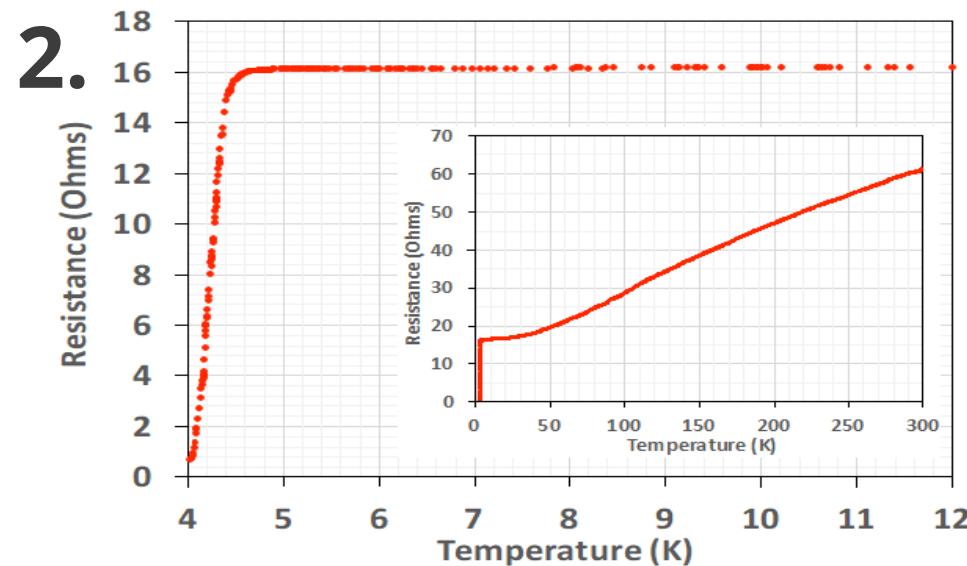
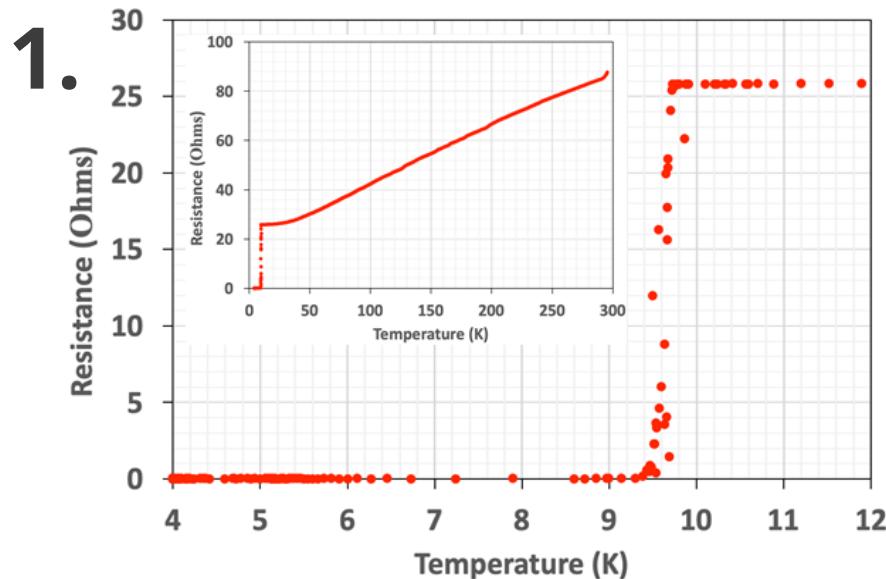


Thickness nm	Stress MPa	Rs Ω/sq	Ar sccm	Power W	mT	BulkR nΩ-m
341.3	50.7	2.38	43	150	8	812.3
335.3	46.1	2.40	43	150	8	804.7
274.0	822.6	0.89	22.5	225	4.5	243.9
294.4	797.2	0.83	22.5	225	4.5	244.4
267.5	802.6	0.86	22.5	225	4.5	230.1
262.5	642.5	1.05	22.5	225	4.5	275.6

Sputter deposition parameters and resulting stress and room-temperature resistivity measurements.

As the power increases from 160 W to 240 W and chamber pressure decreases from 8 mTorr to 4.5 mTorr and argon (Ar) gas flows decrease from 43.3 sccm to 22.9 sccm, transition temperature of the Nb is higher, closer to 10 K, which provides a greater contrast to that of the Sn. The transition temperature of Sn is 3.7 K. We attribute the difference to film stress, which is correlated with room-temperature resistivity

Optimization superconductivity of nanostructured Nb films



Row Number	DC Power (W)	Argon Flow Rate (sccm)	Pressure (mTorr)	d_{Nb} (nm)	σ_{Nb} (MPa)	\mathfrak{R}_{Nb} (Ω/\square)	ρ_{Nb} ($n\Omega \cdot m$)	ℓ_{Nb} (\AA)	T_c (K)
1	225	22.5	4.5	274	823	0.89	244	36	9.6
2	150	43.0	8.0	341	51	2.38	812	11	4.2

Experimental data showing the resistance as a function of temperature for sputtered niobium. For (a) the transition temperature near 4 Kelvin is so low that it could interfere with the transition for tin (approximately 3.7 Kelvin in bulk). For (b) the transition temperature is near the expected bulk value and well separated from the transition for tin.

References

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Questions?